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10/605,244	09/17/2003	Lance Genicola	FIS920030203	3319
30449	7590	06/23/2005	EXAMINER	
SCHMEISER, OLSEN + WATTS			GARCIA, JOANNIE A	
3 LEAR JET LANE				
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EXAMINER

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Commissioner for Patents

The following change has been made via Examiner's Amendment:

In the Specification:

Paragraph[0025], line 2, delete FIG. 215 and insert instead --FIG. 5--


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tions of corona discharge DIT measurement tools may be found in United States Patent 5,216,362 to Verkuil and United States Patent 6,037,797 to Lagowski et al. both of which are hereby incorporated by reference in their entirety.

0.C.
6/20/2005

[0025] FIG. 5 is a schematic diagram of a system for practicing the present invention. In FIG. ~~215~~⁵ a cluster tool 215 includes a hub 220 attached to which are a wafer load/unload station 225, a clean and wet etch tool 2305, a RTO tool 235 having a chamber for forming a first dielectric layer, an ion implantation tool 240, a gate dielectric tool 245 having a chamber for forming a second dielectric layer and DIT measurement tool 170 are attached. A wafer handing mechanism 250 in hub 220 can move a wafer between any of wafer load/unload station 225, clean and wet etch tool 230, RTO tool 235, ion implantation tool 240, gate dielectric tool 245 and DIT measurement tool 170.

[0026] In one example, clean and wet etch tool 230 may be a spin etch/clean tool. Clean and wet etch tool 230 may be two separate tools. In one example, gate dielectric tool 245 may be an oxidation furnace. A RTNH_3 , RTNO , RTNO_2 or N^* plasma tool may be substituted for ion implant tool